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## Correction: A vertical WSe<sub>2</sub>–MoSe<sub>2</sub> p–n heterostructure with tunable gate rectification

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 Correction for 'A vertical WSe<sub>2</sub>–MoSe<sub>2</sub> p–n heterostructure with tunable gate rectification' by Hailing Liu *et al.*, *RSC Adv.*, 2018, **8**, 25514–25518.

The authors regret that Hailiang Liu's name was spelled incorrectly in the original article; the corrected version is shown above. The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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